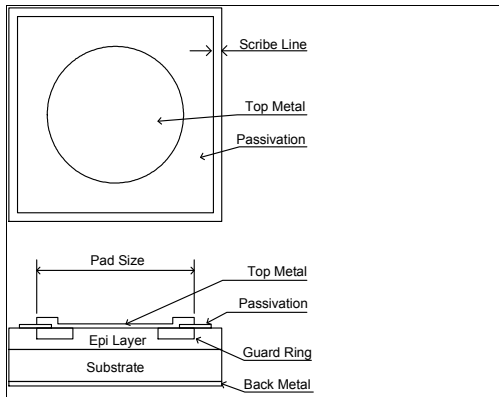


30mA 40V Low VF(0.30mm)



Chip Information

Chip Size	0.30 x 0.30mm
Pad Size	0.13 x 0.13mm
Chip Quantity	122959 pcs/wafer
Scribe Line Width	60um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	30	mA	
Peak Forward Surge Current	IFSM	0.2	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.370	0.360	0.310	V	IF=1mA Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	0.5	0.35	0.13	uA	VR=30V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	42	45	57	V	IR=10uA
Junction Capacitance	Cj			2	pF	V=1V,f=1MHz
Reverse Recovery Time	trr			1	nS	IF=IR=10mA irr=0.1IR

Ordering Information

Chip Type	Chip Thickness	Back Metal
GDSYHF033P	180 +/- 20um	Au(For Eutectic)
GDSYHF034P	150 +/- 20um	Au(For Eutectic)

Note:
 Designed For RB751S-40,RB715F